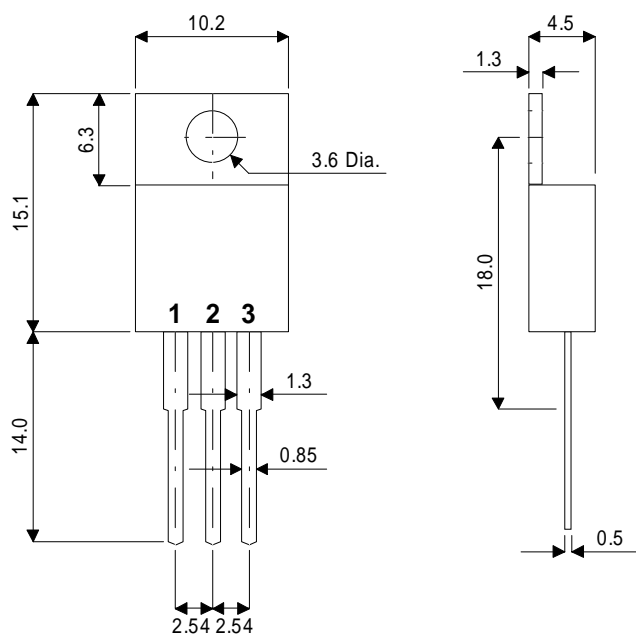


MECHANICAL DATA

Dimensions in mm



TO-220

Pin 1 - Base

Pin 2 - Collector

Pin 3 - Emitter

**ADVANCED
DISTRIBUTED BASE DESIGN
HIGH VOLTAGE
HIGH SPEED NPN
SILICON POWER TRANSISTOR**

Designed for use in
electronic ballast applications

- SEMEFAB DESIGNED AND DIFFUSED DIE
- HIGH VOLTAGE
- HIGH CURRENT
- EFFICIENT POWER SWITCHING

FEATURES

- Multi-base for efficient energy distribution across the chip resulting in significantly improved switching and energy ratings across full temperature range.
- Ion implant and high accuracy masking for tight control of characteristics from batch to batch.
- Triple Guard Rings for improved control of high voltages.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage ($I_E=0$)	1000V
V_{CEO}	Collector – Emitter Voltage ($I_B = 0$)	500V
V_{EBO}	Emitter – Base Voltage ($I_C = 0$)	10V
I_C	Continuous Collector Current	11A
I_B	Base Current	3A
P_{tot}	Total Dissipation at $T_{case} = 25^{\circ}C$	100W
T_j	Junction Temperature	150°C
T_{stg}	Operating and Storage Temperature Range	-55 to +150°C

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
ELECTRICAL CHARACTERISTICS						
$V_{CEO(sus)}$	Collector – Emitter Sustaining Voltage	$I_C = 10mA$	500		V	
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage	$I_C = 1mA$	1000			
$V_{(BR)EBO}$	Emitter – Base Breakdown Voltage	$I_E = 1mA$	10			
I_{CBO}	Collector – Base Cut-Off Current	$V_{CB} = 1000V$		10	μA	
			$T_C = 125^{\circ}C$	100		
I_{CEO}	Collector – Emitter Cut-Off Current	$V_{CE} = 490V$		100	μA	
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 9V$		10	μA	
			$T_C = 125^{\circ}C$	100		
h_{FE}^*	DC Current Gain	$I_C = 0.1A$	$V_{CE} = 1V$	15	40	—
		$I_C = 3A$	$V_{CE} = 1V$	5	20	
		$I_C = 0.5A$	$V_{CE} = 5V$	18	45	
		$I_C = 3A$	$V_{CE} = 5V$	8	20	
$V_{CE(sat)}^*$	Collector – Emitter Saturation Voltage	$I_C = 1A$	$I_B = 0.1A$		0.3	V
		$I_C = 2A$	$I_B = 0.4A$		0.5	
		$I_C = 5A$	$I_B = 1A$		1.0	
$V_{BE(sat)}^*$	Base – Emitter Saturation Voltage	$I_C = 3A$	$I_B = 0.3A$		1.2	V
		$I_C = 5A$	$I_B = 1A$		1.5	
DYNAMIC CHARACTERISTICS						
f_t	Transition Frequency	$I_C = 0.2A$	$V_{CE} = 4V$		16	MHz
C_{ob}	Output Capacitance	$V_{CB} = 10V$	$f = 1MHz$		85	pF

* Pulse test $t_p = 300\mu s$, $\delta < 2\%$